



# PSMN4R3-30BL

N-channel 30 V 4.1 mΩ logic level MOSFET in D2PAK

Rev. 1 — 22 March 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

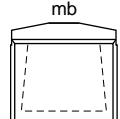
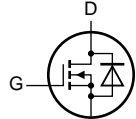
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a> <a href="#">[1]</a>	-	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	103	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 100\text{ °C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	4.9	5.8	mΩ
		$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ °C}$ ; see <a href="#">Figure 13</a>	-	3.5	4.1	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 15\text{ A}; V_{DS} = 15\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	5	-	nC
$Q_{G(tot)}$	total gate charge		-	19	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; I_D = 100\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega$ ; unclamped	-	-	74	mJ

[1] Continuous current is limited by package.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain <sup>[1]</sup>		
3	S	source		
mb	D	mounting base; connected to drain		

SOT404 (D2PAK)

[1] It is not possible to make connection to pin 2

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R3-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R3-30BL	PSMN4R3-30BL

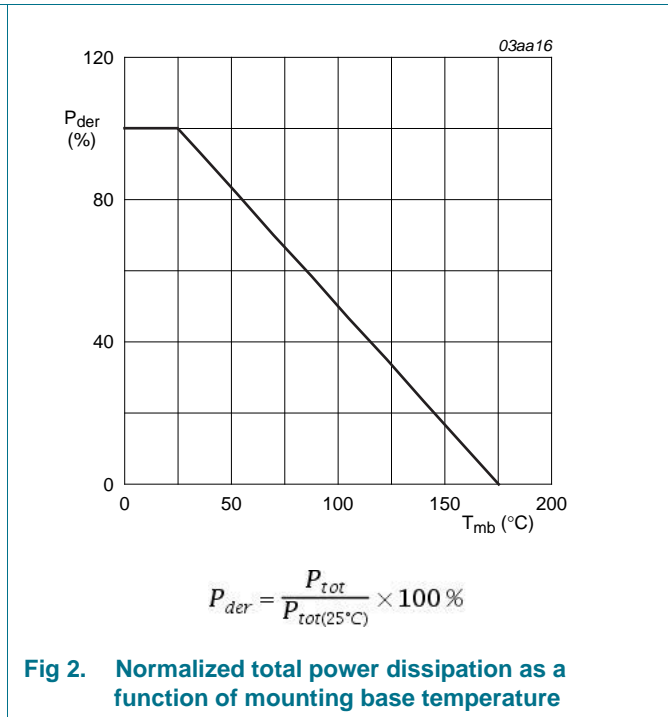
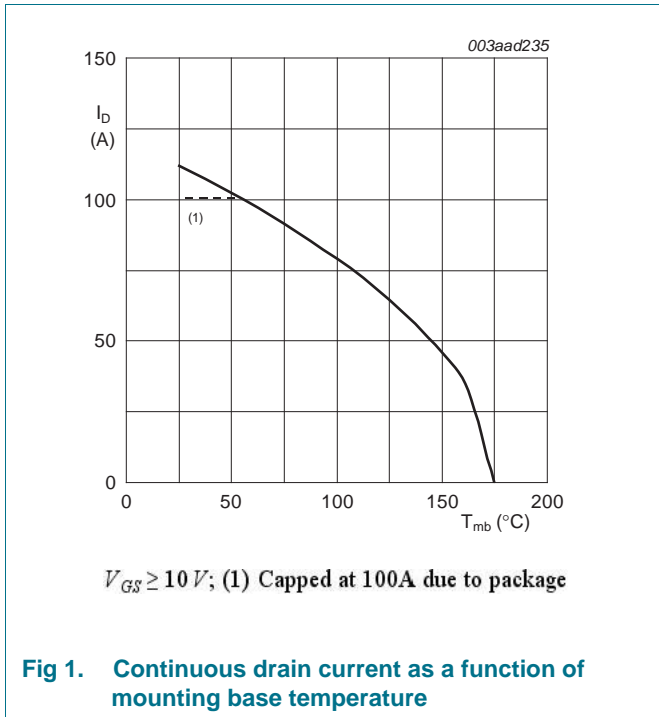
## 5. Limiting values

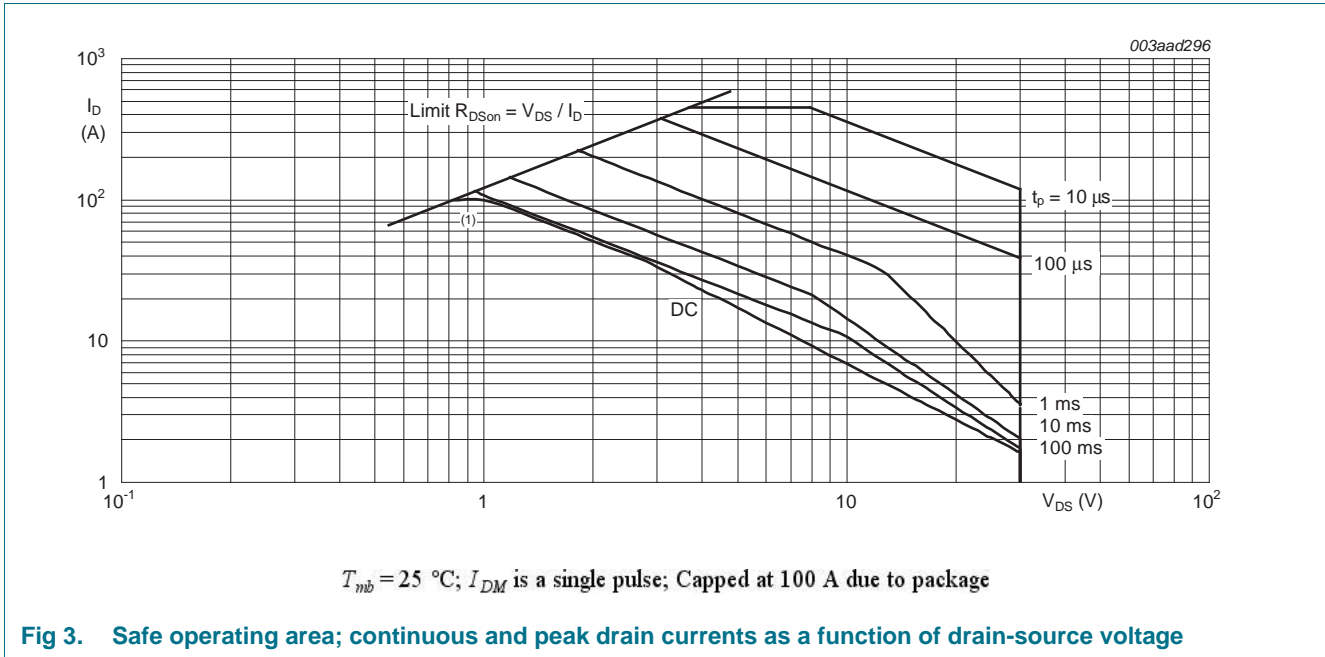
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a> <sup>[1]</sup>	-	80	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a> <sup>[1]</sup>	-	100	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	465	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	103	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C <sup>[1]</sup>	-	100	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	465	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 100 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; unclamped	-	74	mJ

[1] Continuous current is limited by package.

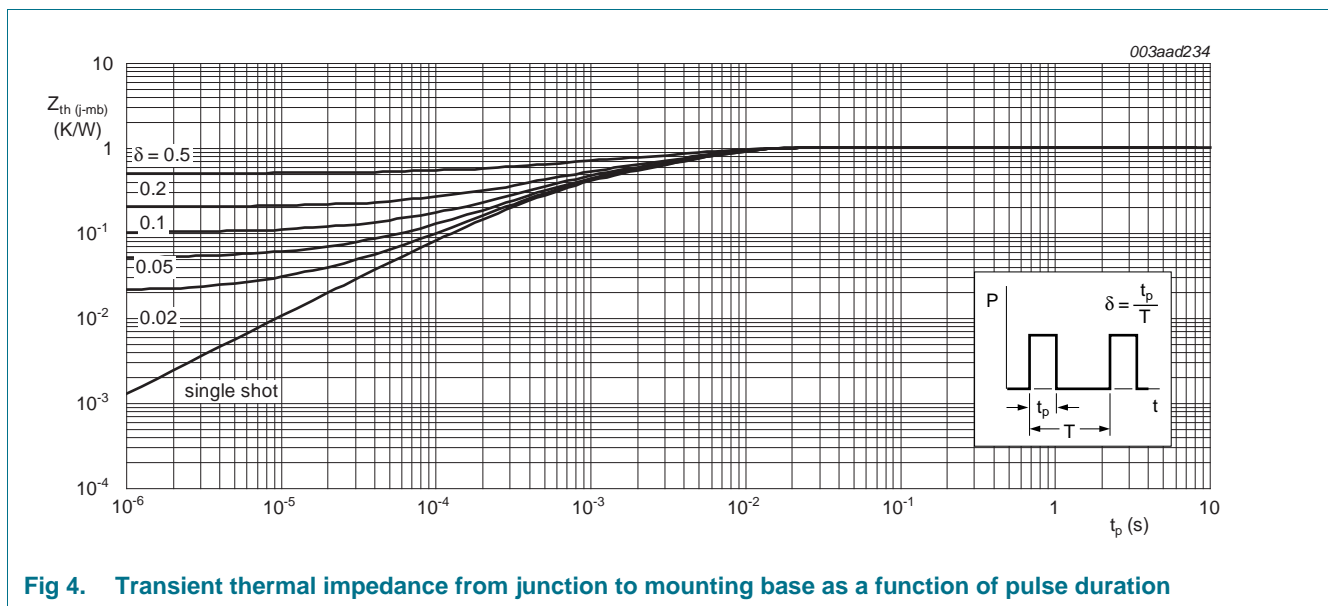




## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	1	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 7. Characteristics

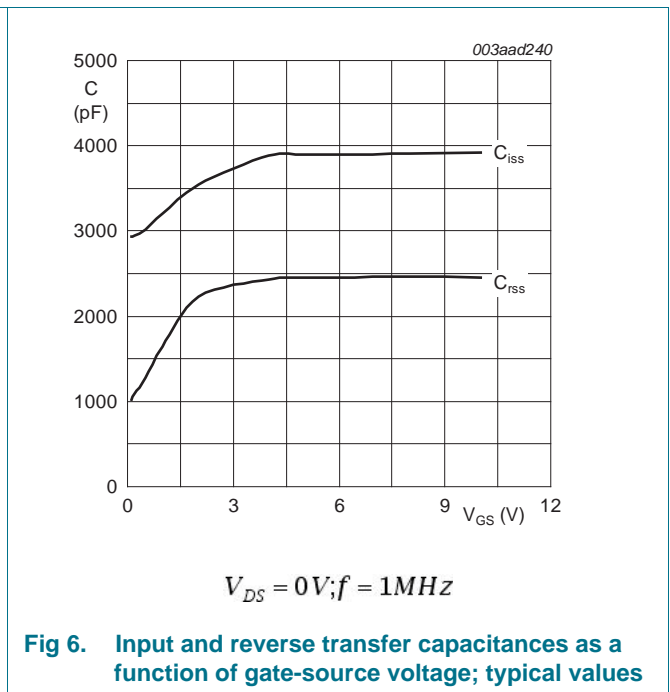
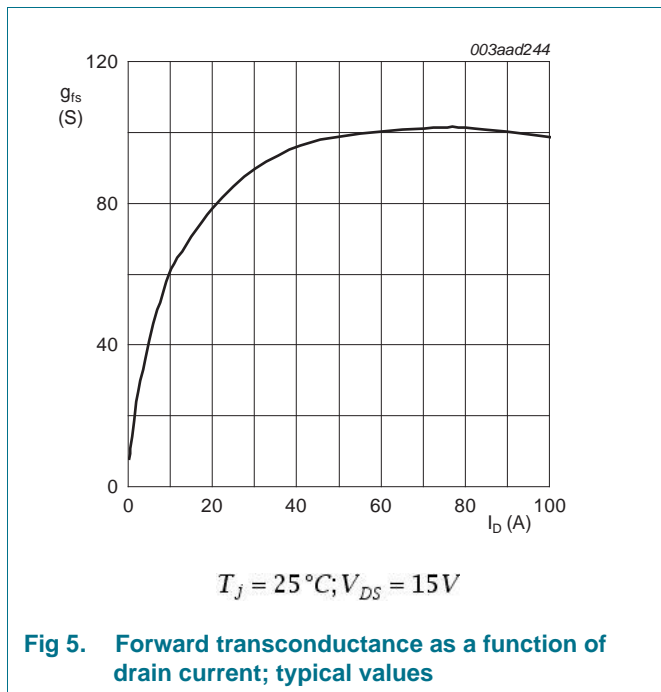
**Table 7. Characteristics**

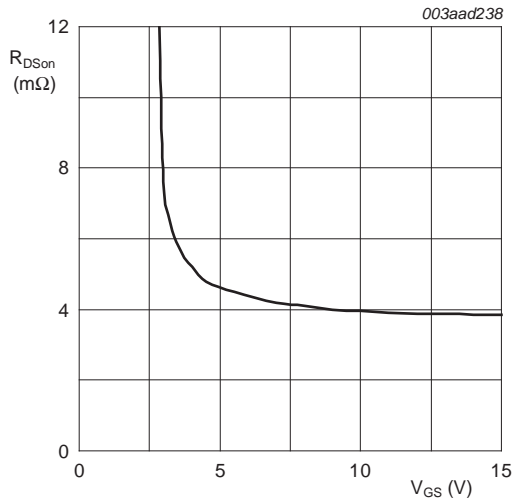
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	-	-	2.45	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.02	1	$\mu A$
		$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 125 \text{ }^\circ C$	-	-	40	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	10	100	nA
		$V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 15 A; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	6.65	7.8	mΩ
		$V_{GS} = 4.5 V; I_D = 15 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 13</a>	-	4.46	5.2	mΩ
		$V_{GS} = 10 V; I_D = 15 A; T_j = 100 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	4.9	5.8	mΩ
		$V_{GS} = 10 V; I_D = 15 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 13</a>	-	3.5	4.1	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	1	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 15 A; V_{DS} = 15 V; V_{GS} = 4.5 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	19	-	nC
		$I_D = 15 A; V_{DS} = 15 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	41.5	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	30	-	nC
$Q_{GS}$	gate-source charge	$I_D = 15 A; V_{DS} = 15 V; V_{GS} = 4.5 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	8	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	4	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	4	-	nC
$Q_{GD}$	gate-drain charge		-	5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 15 A; V_{DS} = 15 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	2.7	-	V
$C_{iss}$	input capacitance	$V_{DS} = 15 V; V_{GS} = 0 V; f = 1 \text{ MHz}$ ;	-	2400	-	pF
$C_{oss}$	output capacitance	$T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 16</a>	-	500	-	pF
$C_{rss}$	reverse transfer capacitance		-	240	-	pF

**Table 7. Characteristics ...continued**  
 Tested to JEDEC standards where applicable.

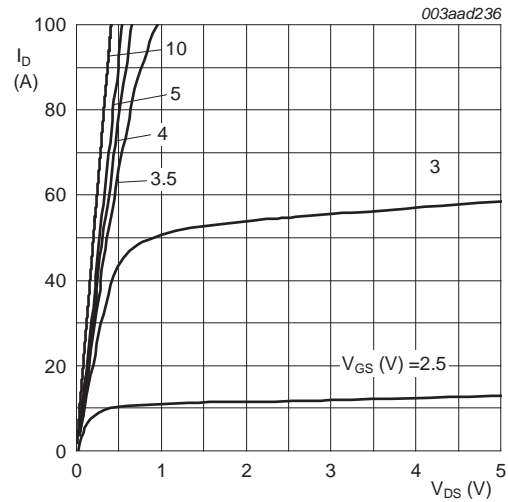
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 0.5\ \Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 5.6\ \Omega$	-	28	-	ns
$t_r$	rise time		-	58	-	ns
$t_{d(off)}$	turn-off delay time		-	44	-	ns
$t_f$	fall time		-	21	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 17</a>	-	0.81	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 15\text{ A}; dI_S/dt = -100\text{ A}/\mu\text{s};$	-	35	-	ns
$Q_r$	recovered charge	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}$	-	30	-	nC





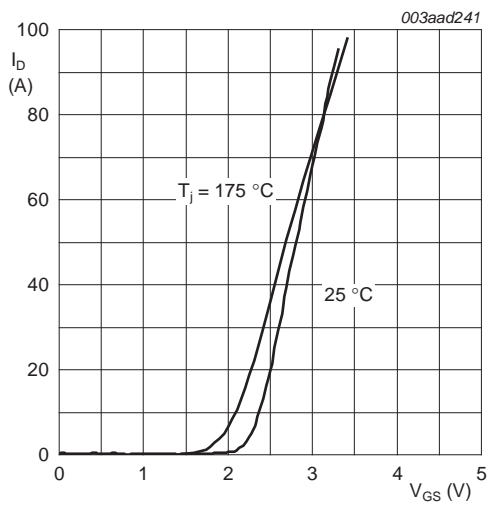
$T_j = 25\text{ }^\circ\text{C}; I_D = 15\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



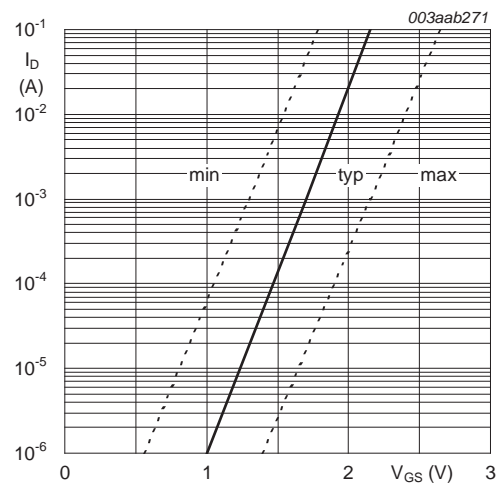
$T_j = 25\text{ }^\circ\text{C}$

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



$V_{DS} > I_D \times R_{DS(on)}$

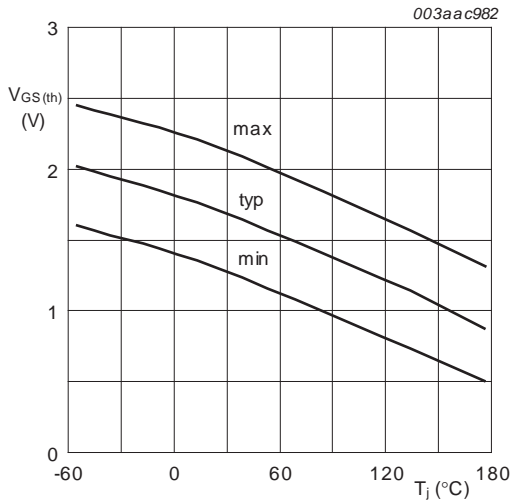
Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

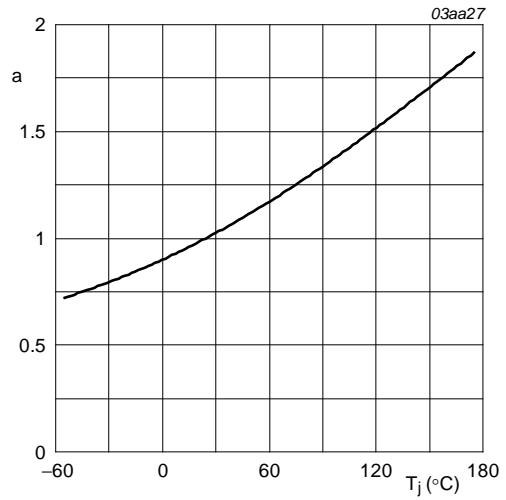
Fig 10. Sub-threshold drain current as a function of gate-source voltage





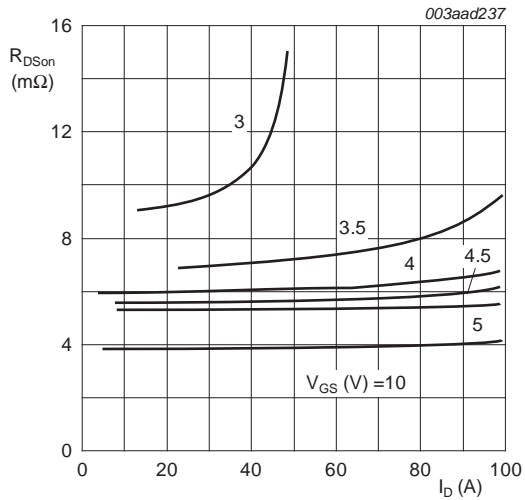
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

Fig 11. Gate-source threshold voltage as a function of junction temperature



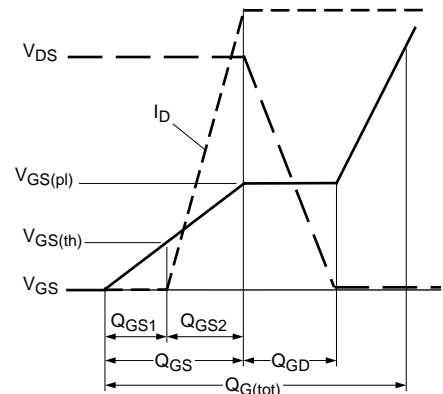
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



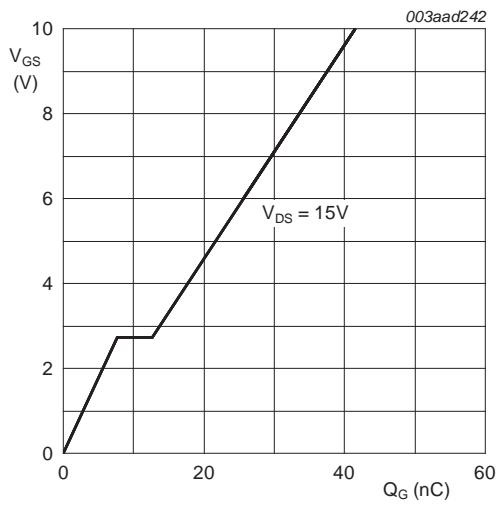
$$T_j = 25^\circ\text{C}$$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values



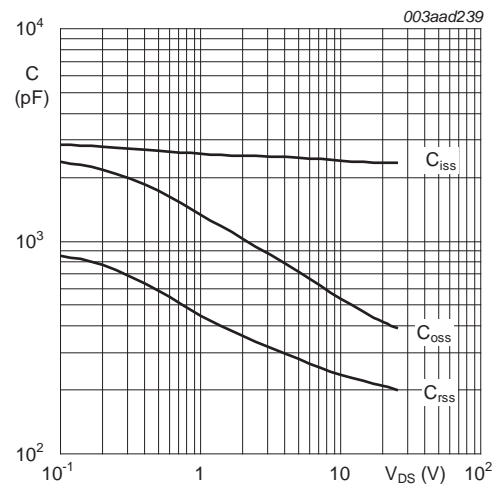
003aaa508

Fig 14. Gate charge waveform definitions



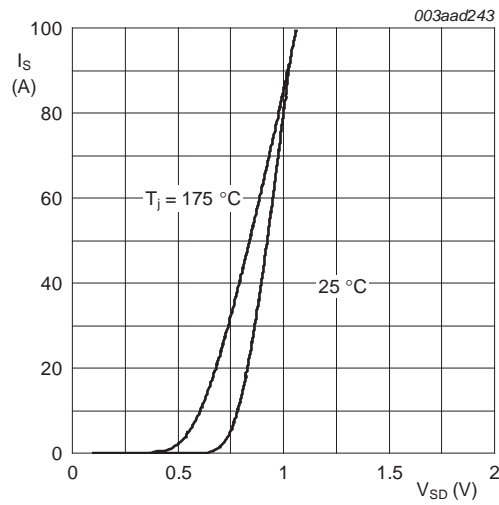
$T_j = 25^\circ C; I_D = 15A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 17. Source current as a function of source-drain voltage; typical values

8. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



Fig 18. Package outline SOT404 (D2PAK)

## 9. Revision history

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**Table 8.** Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R3-30BL v.1	20120322	Product data sheet	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status <sup>[1]</sup> [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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## 12. Contents

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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